
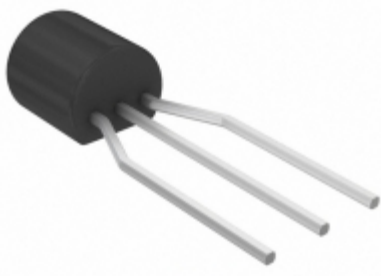


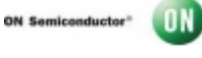





	<h2>BS108ZL1G</h2>
	<p><b>Hersteller-Teilenummer:</b> <a href="#">BS108ZL1G</a></p> <p><b>Hersteller / Marke:</b> <a href="#">AMI Semiconductor / ON Semiconductor</a></p> <p><b>Teil der Beschreibung:</b> MOSFET N-CH 200V 0.25A TO-92</p> <p><b>Datenblätter:</b>  <a href="#">BS108ZL1G.pdf</a></p> <p><b>RoHs Status:</b> Bleifrei / RoHS-konform</p> <p><b>Lagerzustand:</b> New original, 2896 pcs Stock Available.</p> <p><b>Liefern von:</b> Hong Kong</p> <p><b>Versandweg:</b> DHL/Fedex/TNT/UPS/EMS</p>
	
<p>Image may be representation. See specs for product details.</p>	

### Spezifikationen

Teilenummer	BS108ZL1G
Hersteller	AMI Semiconductor / ON Semiconductor
Beschreibung	MOSFET N-CH 200V 0.25A TO-92
Kategorie	<a href="#">Diskrete Halbleiterprodukte &gt; Transistoren-FETs,</a>
Teilstatus	2896 pcs Stock
Serie	-
Technologie	MOSFET (Metal Oxide)
Betriebstemperatur	-55°C ~ 150°C (TJ)
Befestigungsart	Through Hole
Verpackung / Gehäuse	TO-226-3, TO-92-3 (TO-226AA) (Formed Leads)
Supplier Device-Gehäuse	TO-92-3
Verlustleistung (max)	350mW (Ta)
Typ FET	N-Channel
FET-Merkmal	-
Drain-Source-Spannung (Vdss)	200V
Strom - Ununterbrochener Abfluss (Id) bei 25 ° C	250mA (Ta)
Rds On (Max) @ Id, Vgs	8 Ohm @ 100mA, 2.8V
VGS (th) (Max) @ Id	1.5V @ 1mA
Gate Charge (Qg) (Max) @ Vgs	-
Eingabekapazität (Ciss) (Max) @ Vds	150pF @ 25V
Verpackung	Cut Tape (CT)

BS108ZL1G ist neu im Original, Suche BS108ZL1G Datenblätter, PDF, Inventar bei Y-IC.com Online, Bestellen Sie BS108ZL1G AMI Semiconductor / ON Semiconductor mit Garantie und Vertrauen. Anfrage BS108ZL1G: [Info@Y-IC.com](mailto:Info@Y-IC.com)

Sie können auch interessiert sein:

 <p><b>BS120</b> Sharp Microelectronics PHOTODIODE BLUE SENS 1.55MM SQ</p>	 <p><b>BS107PSTZ</b> Diodes Incorporated MOSFET N-CH 200V 0.12A TO92-3</p>	 <p><b>BS108G</b> AMI Semiconductor / ON Semiconductor MOSFET N-CH 200V 0.25A TO- 92</p>	 <p><b>BS107PSTOB</b> Diodes Incorporated MOSFET N-CH 200V 0.12A TO92-3</p>
 <p><b>BS1100N-A1</b> BENCENT BENCENT DO-214A</p>	 <p><b>BS108/01,126</b> NXP Semiconductors / Freescale MOSFET N-CH 200V 300MA SOT54</p>	 <p><b>BS12I-22</b> MPD (Memory Protection Devices) 9V SNAP I STYLE 12" WIRE LEADS</p>	 <p><b>BS12I</b> MPD (Memory Protection Devices) SNAPS 9V 12" LEADS I-STYLE</p>

### heiße Teile

Mehr

04023C181KAT2A	12065C224MAZ2A	1210GC102MAT9A	1808SC221MATME	2DI50B-100
AD7982BCPZ-RL7	BL2125LM252-T	BL919518APRT	BS107ARL1G	BS107KL-T1-E3
BS120E0F	BS170FTA	BS170RLRAG	BS1800N-C	C3216X5R1A475K
CY24242OXCT	DDB6U60N1000K	DMN6040SSS-13	EXA40-24S05-V	GRM1555C1H9R8CZ01D
ICL828IH-T	IDT74FCT244ATSO	KSD1616A-G	LM10540MHX/NOPB	LM340SX-5
LSP1084K15AG	LTC1044CN8	LTC1773EMS#TRPBF	MAX8808ZETA+	MMZ0603F100CT000
N25Q128A13ESED0F	P270CH04FP0	P6SMB300A-E3/52	PI74FCT16244TVEX	PM30CTJ-060-3
RT8863GQW	RT9167-17PB	RT9379BGQW	S1D13775B00B60L	S1M8656A01-F0T0
SC100C20	SC1405TS	SD5491-004	SI2306BDS	SI4922BDY-T1-E3
SKB50-12A3	SMF30CAT1G	SPB03N60C3	STGD7NB60ST4	VI-26Z-CX

Contact us: [Info@Y-IC.com](mailto:Info@Y-IC.com)

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